

Fig. 1

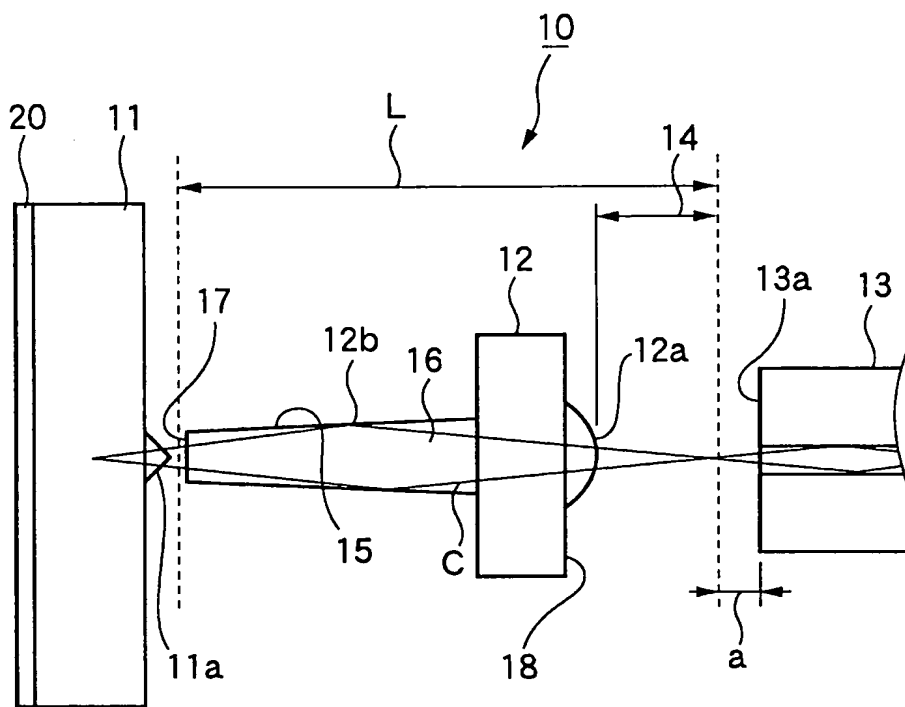


Fig. 2

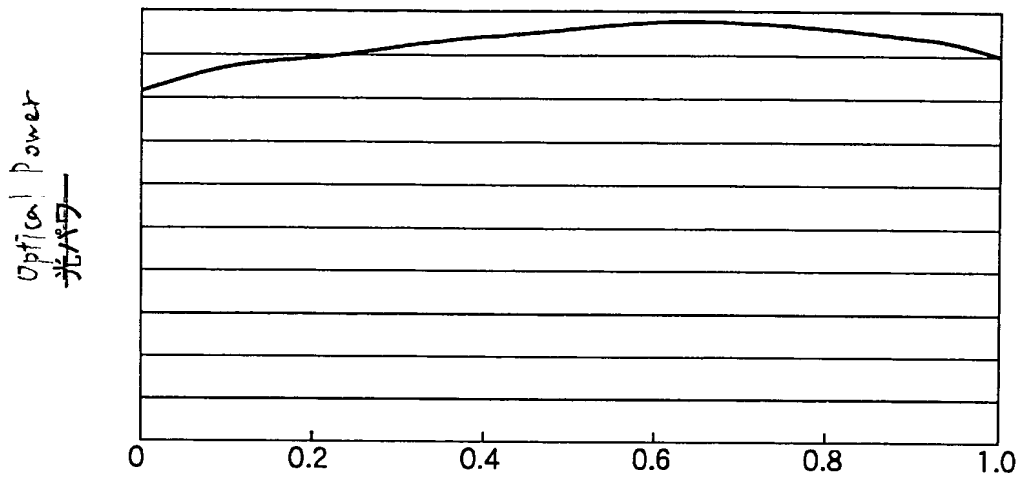
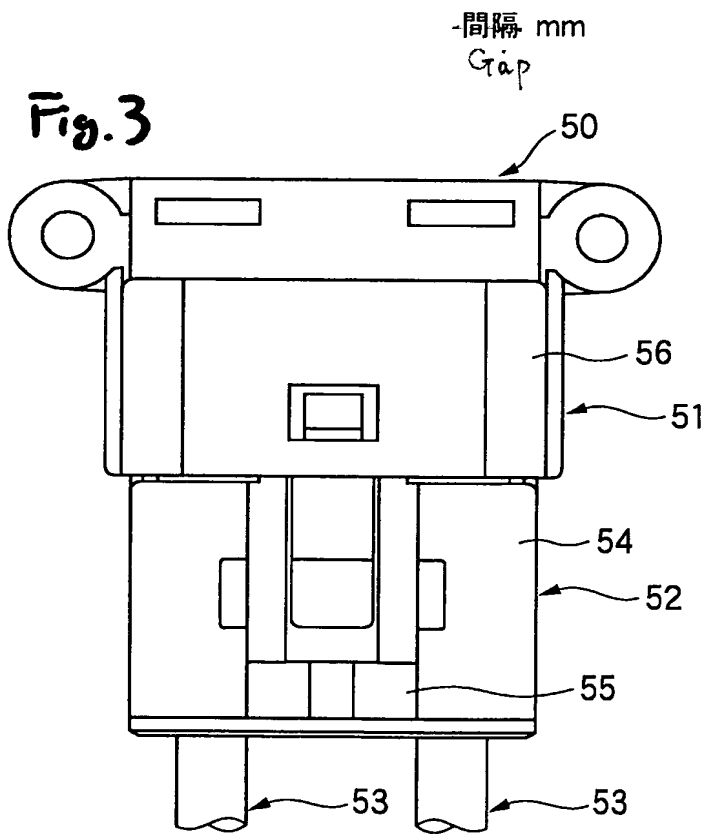


Fig. 3





A detailed cross-sectional diagram of a semiconductor device. The device features a central cavity or well structure. At the top, there is a dome-shaped layer labeled 58. Below it, a thin layer 65 is positioned above a stack of layers 70 and 69. A vertical structure 59 extends from the top down towards the center. To the right, another vertical structure 60 is shown. The main body of the device consists of several regions: a central region 61, side regions 62 and 63, and bottom regions 66 and 67. A hatched area 68 surrounds the central region 61. A curved surface C3 is located at the bottom of the central cavity. Below C3, there are three distinct regions labeled 53a, 53b, and 53c, which are separated by vertical boundaries 71 and 72. These regions are situated above a base layer 73. Arrows indicate specific features or directions within the device.

Fig. 6

